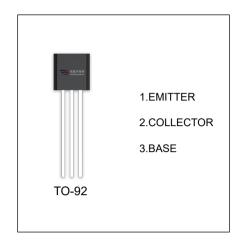


D965 TRANSISTOR (NPN)

FEATURES

- Audio Amplifier
- Flash Unit of Camera
- Switching Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
D965	TO-92	Bulk	1000pcs/Bag
D965-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Para meter Para meter	Value	Unit
V _{CBO}	Collector-Base Voltage	42	V
V _{CEO}	Collector-Emitter Voltage	22	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current -Continuous	5	А
P _D	Collector Power Dissipation	750	mW
R _{θ JA}	Thermal Resistance from Junction to Ambient	166.7	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃



Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	42			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	22			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μΑ, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =30V,I _E =0			0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			0.1	μΑ
	h _{FE(1)}	V _{CE} =2V, I _C = 0.15 mA	150			
DC current gain	h _{FE(2)}	V _{CE} = 2V,I _C = 500 mA	340		2000	
	h _{FE(3)}	V_{CE} =2V, I_C = 2A	150			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3000mA,I _B =100 mA			0.35	V
Transition frequency	f _T	V _{CE} =6V, I _C =50mA,f=30MHz		150		MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	R	Т	V
Range	340-600	560-950	900-2000



